

# UNISONIC TECHNOLOGIES CO., LTD

15N10 **Power MOSFET** 

## 14.7A, 100V (D-S) N-CHANNEL **POWER MOSFET**

### **DESCRIPTION**

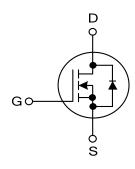
The UTC 15N10 is an N-Channel enhancement MOSFET, it uses UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed and low gate charge.

The UTC 15N10 is suitable for high efficiency switching DC/DC converter, LCD display inverter and load switch.

#### **FEATURES**

- \*  $R_{DS(ON)}$ =0.08 $\Omega$  @ $V_{GS}$ =10V, $I_{D}$ =8A
- \* Low gate charge (Typ=24nC)
- \* Low C<sub>RSS</sub> (Typ=23pF)
- \* High switching speed

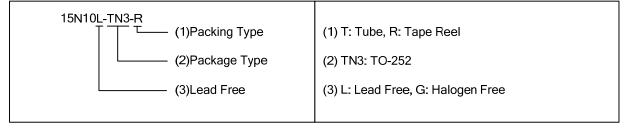
#### **SYMBOL**

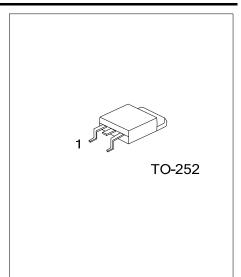


#### **ORDERING INFORMATION**

Ordering Number		Dookono	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
15N10L-TN3-T	15N10G-TN3-T	TO-252	G	D	S	Tube	
15N10L-TN3-R	15N10G-TN3-R	TO-252	G	D	S	Tape Reel	

Pin Assignment: G: Gate D: Drain Note: S: Source





15N10

#### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		$V_{GSS}$	±20	V
	T <sub>C</sub> =25°C, T <sub>J</sub> =150°C	I <sub>D</sub>	14.7	Α
	Continuous $\frac{T_C=25^{\circ}C, T_J=150^{\circ}C}{T_C=70^{\circ}C, T_J=150^{\circ}C}$		13.6	Α
	Pulsed	I <sub>DM</sub>	59	Α
T <sub>C</sub> =25°C			34.7	W
Power Dissipation	T <sub>C</sub> =70°C	P <sub>D</sub>	22.2	W
Operating Junction Temperature		$T_J$	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case (Note)	$\theta_{JC}$	3.6	°C/W

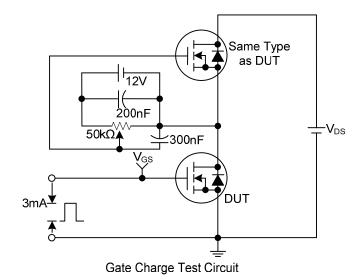
Note: The device mounted on 1in<sup>2</sup> FR4 board with 2 oz copper.

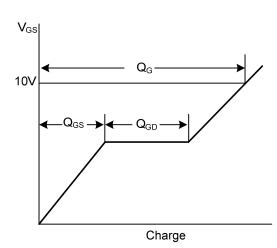
#### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V			
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V			1	μΑ			
Cata Sauraa Laakaga Current	I <sub>GSS</sub>	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V			+100	nΑ			
Gate-Source Leakage Current		V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-100	nΑ			
ON CHARACTERISTICS									
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$			3	V			
Drain-Source On-State Resistance (Note)	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, $I_D$ =8A		80	100	mΩ			
DYNAMIC PARAMETERS									
Input Capacitance	C <sub>ISS</sub>			890		pF			
Output Capacitance	Coss	$V_{GS}$ =0V, $V_{DS}$ =15V, f=1MHz		58		pF			
Reverse Transfer Capacitance	C <sub>RSS</sub>			23		pF			
SWITCHING PARAMETERS									
Total Gate Charge	$Q_G$	V <sub>GS</sub> =10V, V <sub>DS</sub> =80V, I <sub>D</sub> =10A		24		nC			
Total Gate Charge	$Q_G$			13		nC			
Gate to Source Charge	$Q_GS$	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =80V, I <sub>D</sub> =10A		4.6		nC			
Gate to Drain Charge	$Q_GD$			7.6		nC			
Gate-Resistance	$R_G$	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		0.9		Ω			
Turn-ON Delay Time	t <sub>D(ON)</sub>			14		ns			
Rise Time	t <sub>R</sub>	$V_{DS}$ =50V, $R_L$ =5 $\Omega$ , $V_{GEN}$ =10V,		33		ns			
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	$R_G=1\Omega$		39		ns			
Fall-Time	t <sub>F</sub>			5		ns			
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS									
Drain-Source Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =8A, V <sub>GS</sub> =0V		0.9	1.2	V			

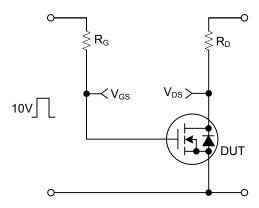
Note: Pulse test: pulse width≤300us, duty cycle≤2%, Guaranteed by design, not subject to production testing.

#### ■ TEST CIRCUITS AND WAVEFORMS

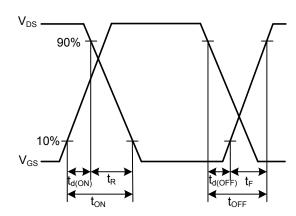




Gate Charge Waveforms

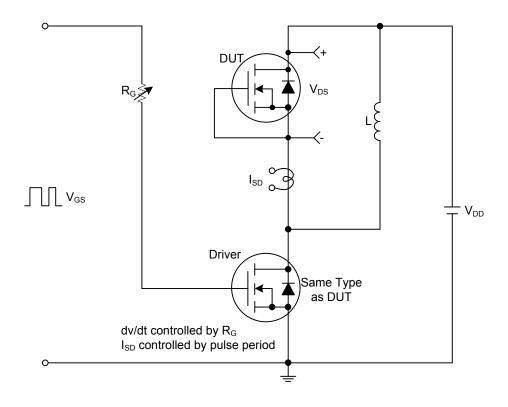


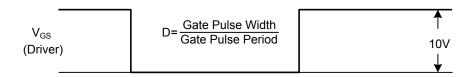
Resistive Switching Test Circuit

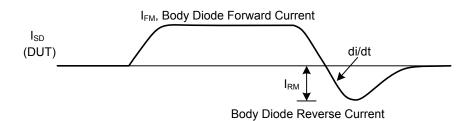


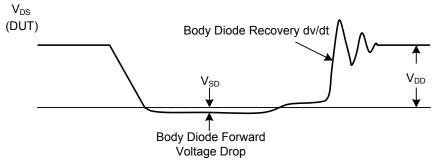
Resistive Switching Waveforms

#### ■ TEST CIRCUITS AND WAVEFORMS



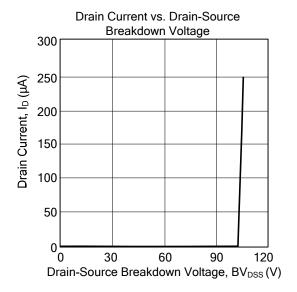


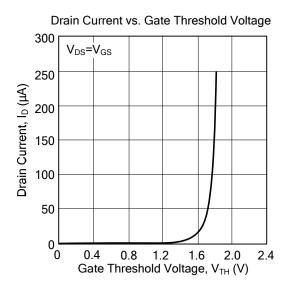


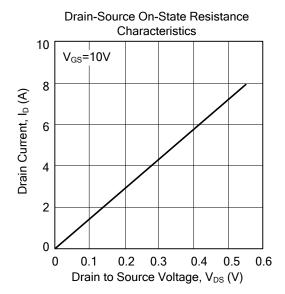


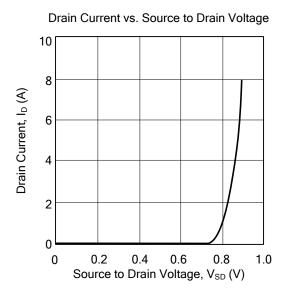
Peak Diode Recovery dv/dt Test Circuit and Waveforms

#### TYPICAL CHARACTERISTICS









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